TOSHIBA

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

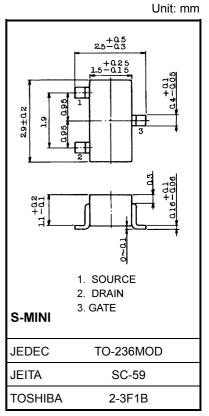
2SK208

General Purpose and Impedance Converter and Condenser Microphone Applications

- High breakdown voltage: $V_{GDS} = -50 V$
- High input impedance: $I_{GSS} = -1.0 \text{ nA} (max) (V_{GS} = -30 \text{ V})$
- Low noise: NF = 0.5dB (typ.) (R_G = $100 \text{ k}\Omega$, f = 120 Hz)
- Small package.

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Gate-drain voltage	V _{GDS}	-50	V
Gate current	lG	10	mA
Drain power dissipation	PD	100	mW
Junction temperature	Тј	125	°C
Storage temperature range	T _{stg}	-55~125	°C



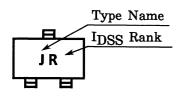
Electrical Characteristics (Ta = 25°C)

Weight: 0.012 g (typ.)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate cut-off current	I _{GSS}	$V_{GS} = -30 \text{ V}, \text{ V}_{DS} = 0$	_	_	-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS} = 0, I_G = -100 \ \mu A$	-50	_	_	V
Drain current	I _{DSS} (Note)	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0$	0.3	_	6.5	mA
Gate-source cut-off voltage	V _{GS (OFF)}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 0.1 \mu\text{A}$	-0.4	_	-5.0	V
Forward transfer admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ kHz}$	1.2	_	_	mS
Input capacitance	C _{iss}	$V_{DS} = 10 \text{ V}, \text{ V}_{GS} = 0, \text{ f} = 1 \text{ MHz}$	_	8.2	_	pF
Reverse transfer capacitance	C _{rss}	$V_{GD} = -10 \text{ V}, \text{ I}_{D} = 0, \text{ f} = 1 \text{ MHz}$	_	2.6	_	pF
Noise figure	NF	V_{DS} = 15 V, V_{GS} = 0 R _G = 100 kΩ, f = 120 Hz	_	0.5	_	dB

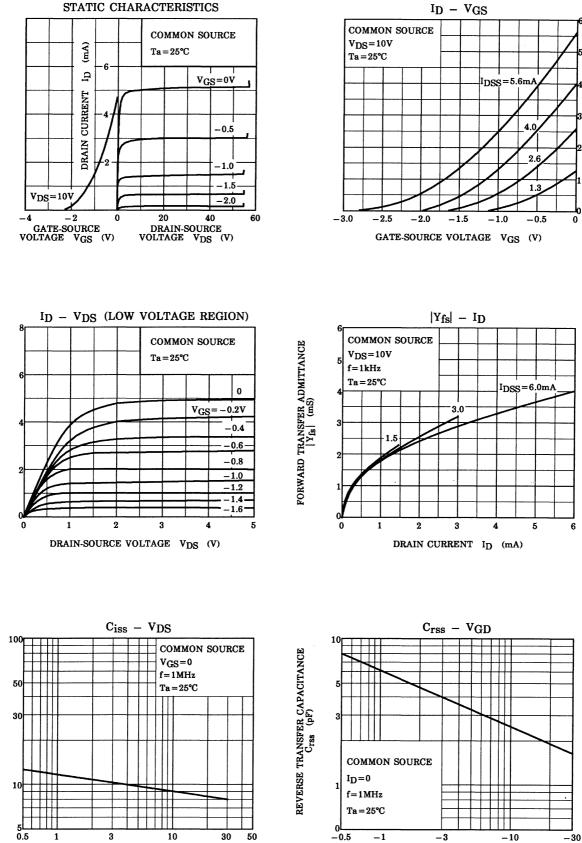
Note: I_{DSS} classification R: 0.30~0.75 mA, O: 0.60~1.40 mA, Y: 1.2~3.0 mA, GR: 2.6~6.5 mA

Marking



(WW)

DRAIN CURRENT ID



2003-03-27

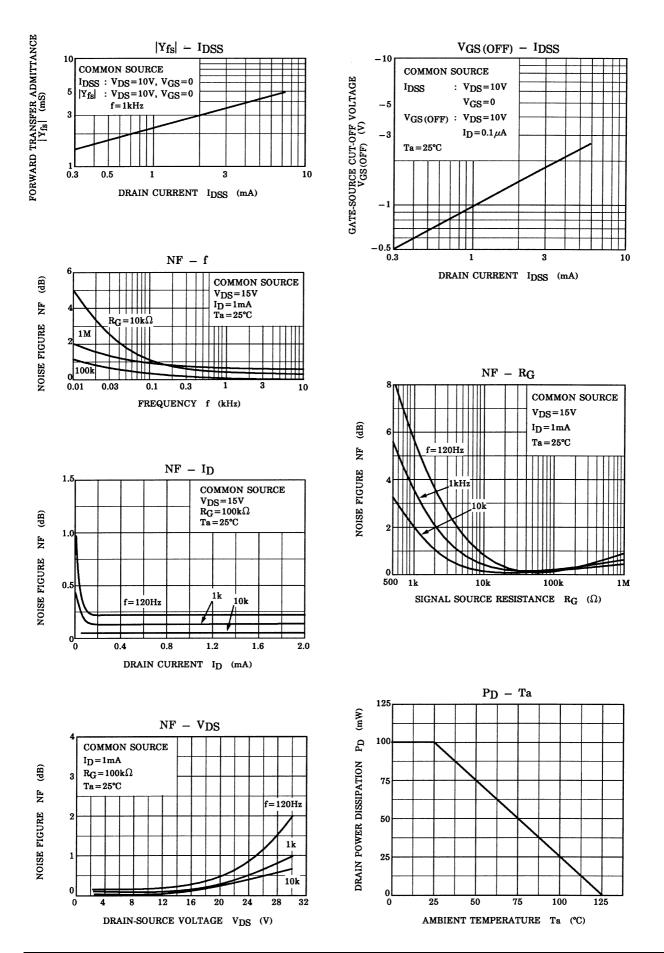
(PF)

INPUT CAPACITANCE Ciss

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DRAIN-SOURCE VOLTAGE V_{DS} (V)

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